

BC846 series

65 V, 100 mA NPN general-purpose transistors

Rev. 9 — 25 September 2012

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number ^[1]	Package			PNP complement
	NXP	JEITA	JEDEC	
BC846	SOT23	-	TO-236AB	BC856
BC846W	SOT323	SC-70	-	BC856W
BC846T	SOT416	SC-75	-	BC856T

[1] Valid for all available selection groups.

1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Two different gain selections

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

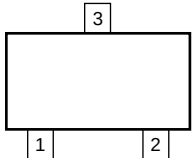
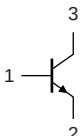
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	65	V
I_C	collector current		-	-	100	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	450	
	h_{FE} group A		110	180	220	
	h_{FE} group B		200	290	450	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT23, SOT323, SOT416			
1	base	 006aaa144	 sym021
2	emitter		
3	collector		

3. Ordering information

Table 4. Ordering information

Type number ^[1]	Package		
	Name	Description	Version
BC846	-	plastic surface-mounted package; 3 leads	SOT23
BC846W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BC846T	SC-75	plastic surface-mounted package; 3 leads	SOT416

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC846	1D*
BC846A	1A*
BC846B	1B*
BC846W	1D*
BC846AW	1A*
BC846BW	1B*
BC846T	1M
BC846AT	1A
BC846BT	1B

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	65	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I_C	collector current		-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]		
	SOT23		-	250	mW
	SOT323		-	200	mW
	SOT416		-	150	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	SOT23		-	-	500	K/W
	SOT323		-	-	625	K/W
	SOT416		-	-	833	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

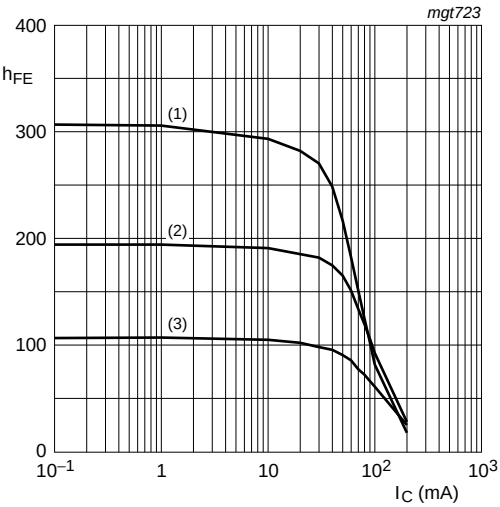
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 10\text{ }\mu\text{A}$				
	h_{FE} group A		-	180	-	
	h_{FE} group B		-	290	-	
	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	450	
	h_{FE} group A		110	180	220	
	h_{FE} group B		200	290	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	90	200	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[1] -	200	400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	[2] -	760	-	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[2] -	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	[3] 580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	[3] -	-	770	mV
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_E = 0\text{ A}; f = 1\text{ MHz}$	-	2	3	pF
C_e	emitter capacitance	$V_{EB} = 0.5\text{ V}; I_C = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	11	-	pF
NF	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	-	2	10	dB

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta = 0.02$.

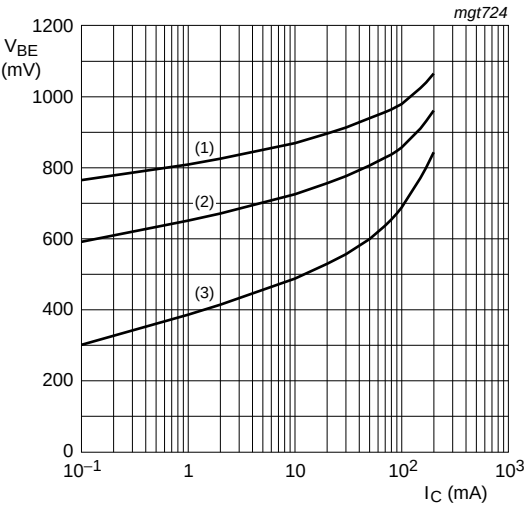
[2] V_{BEsat} decreases by approximately 1.7 mV/K with increasing temperature.

[3] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



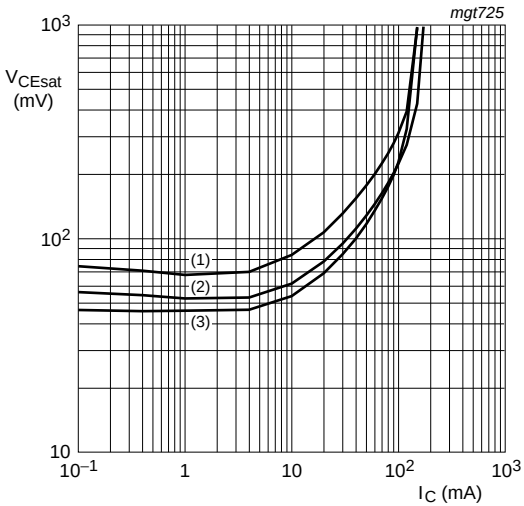
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 1. Selection A: DC current gain as a function of collector current; typical values



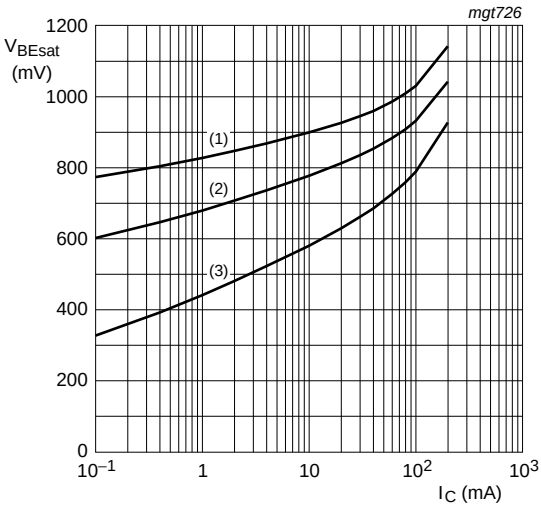
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 2. Selection A: Base-emitter voltage as a function of collector current; typical values



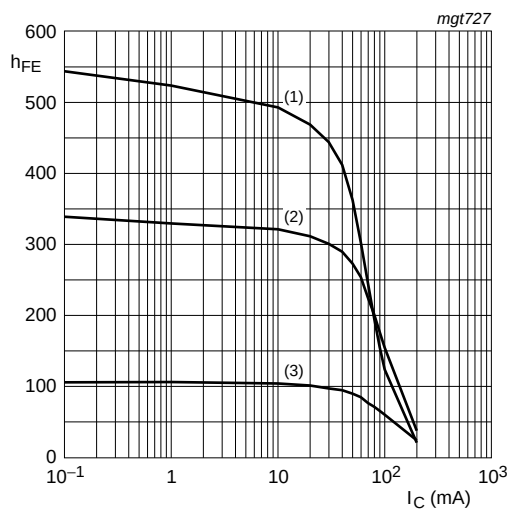
$I_C/I_B = 20$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 3. Selection A: Collector-emitter saturation voltage as a function of collector current; typical values



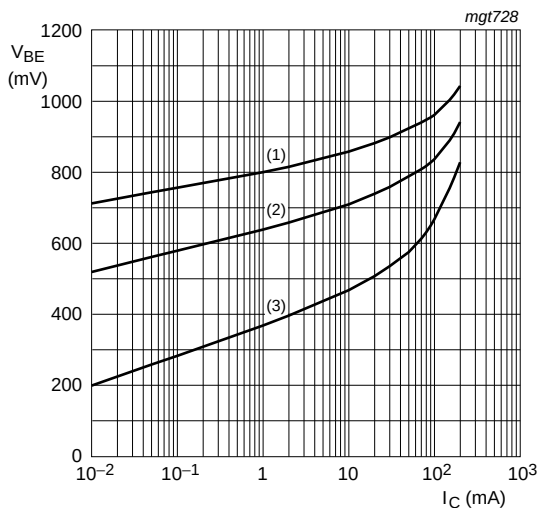
$I_C/I_B = 10$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 4. Selection A: Base-emitter saturation voltage as a function of collector current; typical values



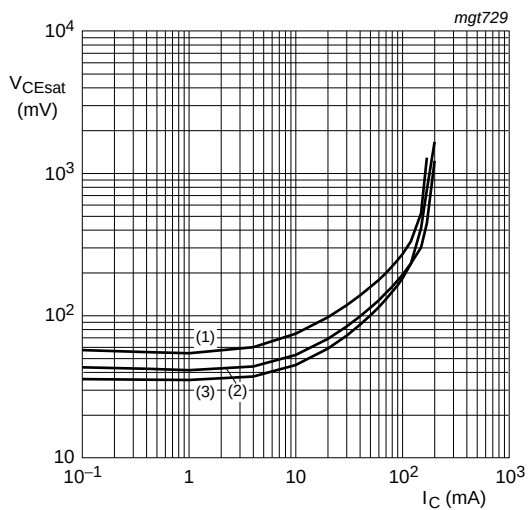
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. Selection B: DC current gain as a function of collector current; typical values



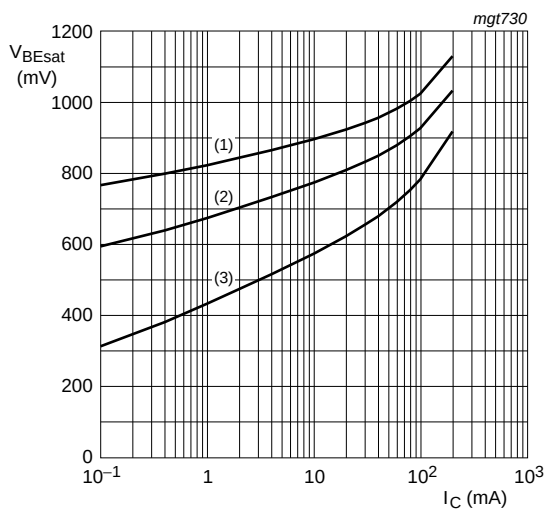
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 6. Selection B: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

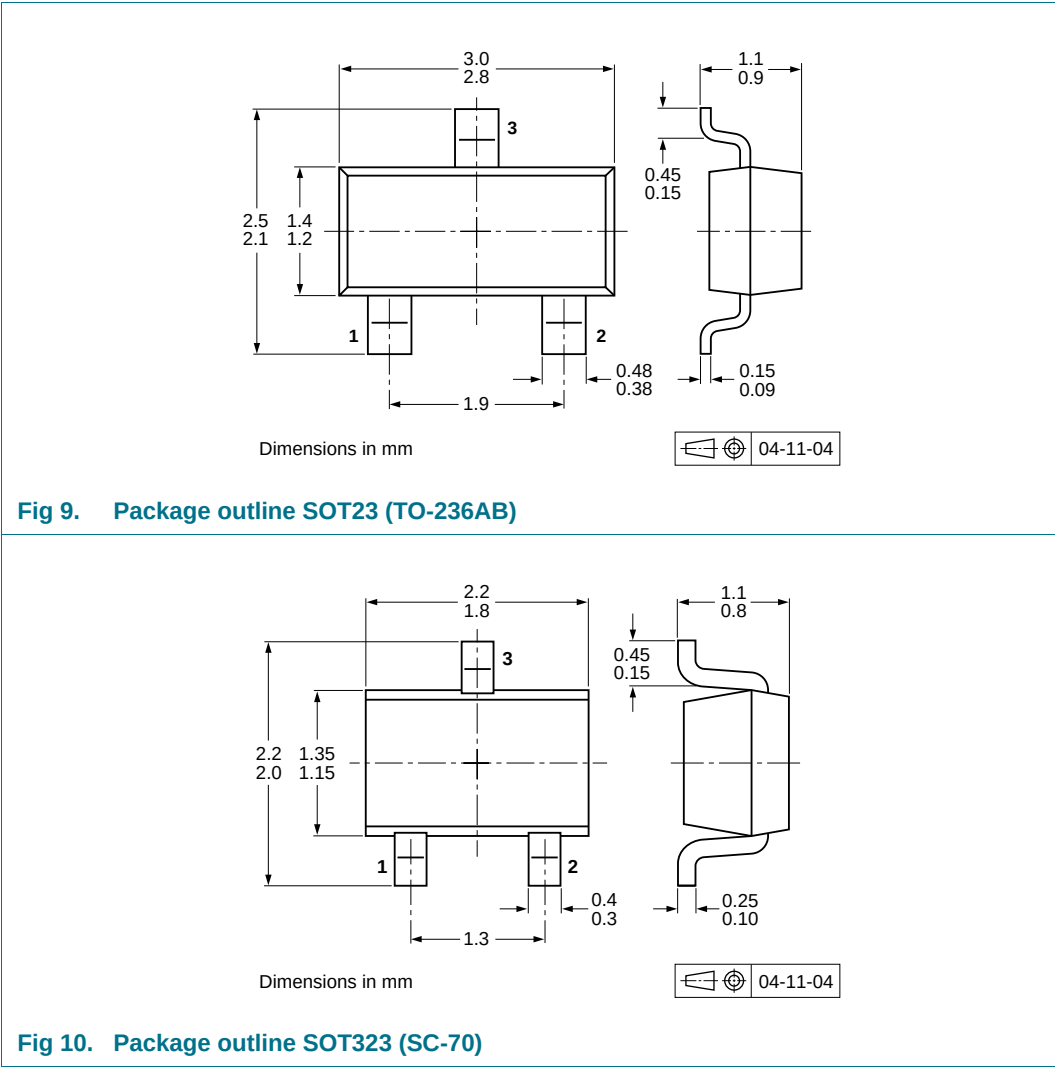
Fig 7. Selection B: Collector-emitter saturation voltage as a function of collector current; typical values

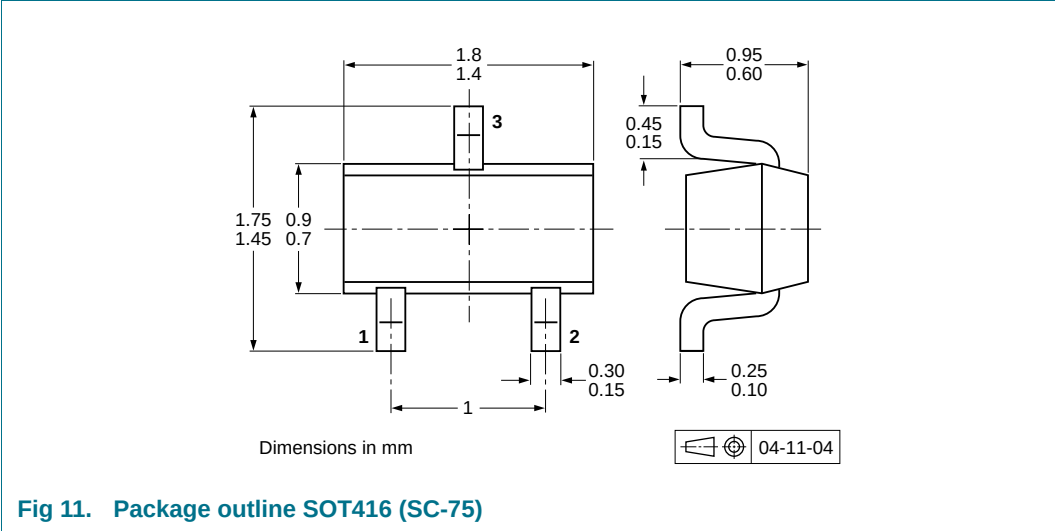


$I_C/I_B = 10$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 8. Selection B: Base-emitter saturation voltage as a function of collector current; typical values

8. Package outline





9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number ^[2]	Package	Description	Packing quantity		
			1000	3000	4000
BC846	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
BC846W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135
BC846T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see [Section 13](#).

[2] Valid for all available selection groups.

10. Soldering

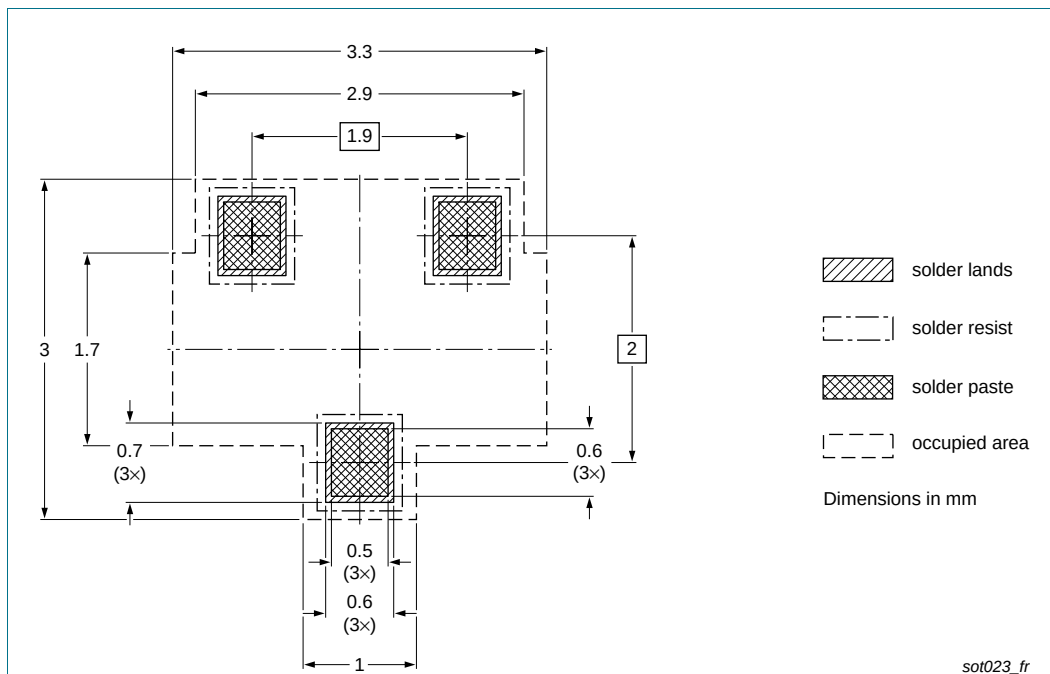


Fig 12. Reflow soldering footprint SOT23 (TO-236AB)

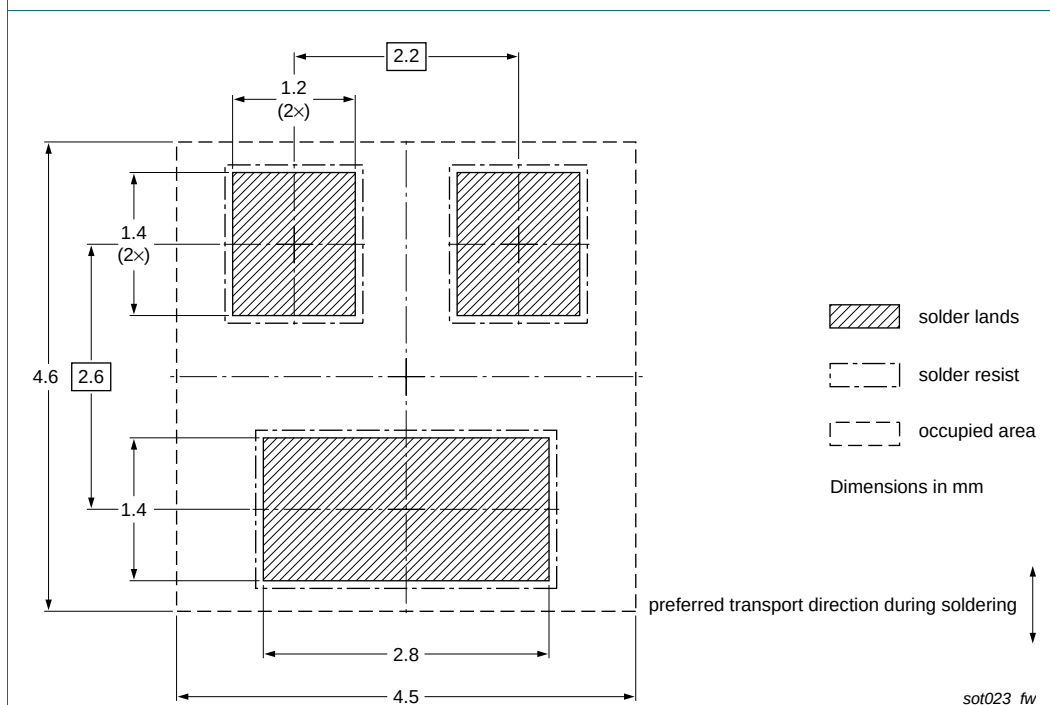


Fig 13. Wave soldering footprint SOT23 (TO-236AB)

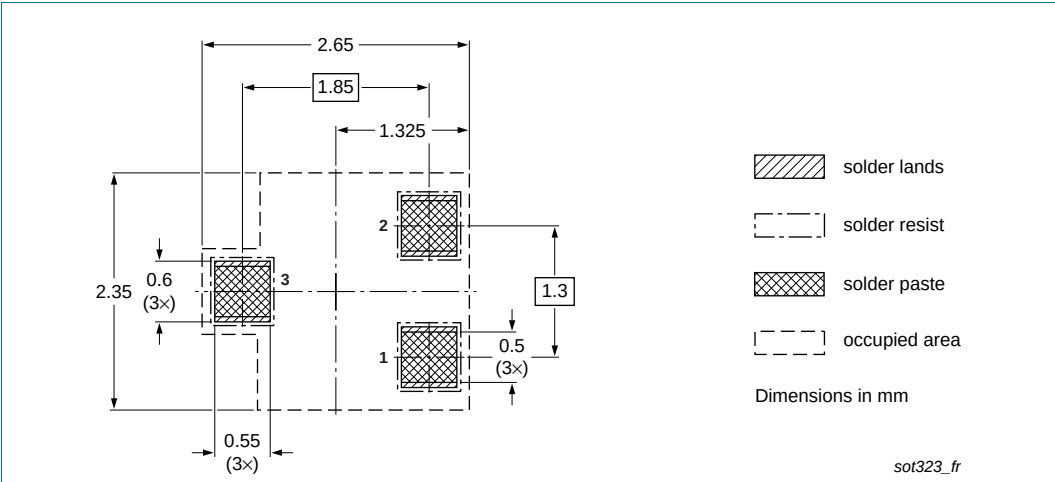


Fig 14. Reflow soldering footprint SOT323 (SC-70)

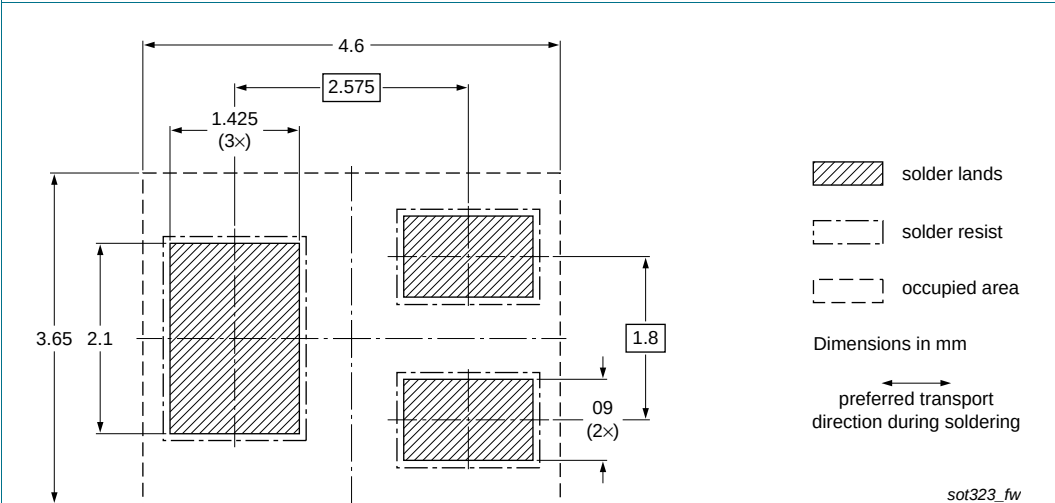


Fig 15. Wave soldering footprint SOT323 (SC-70)

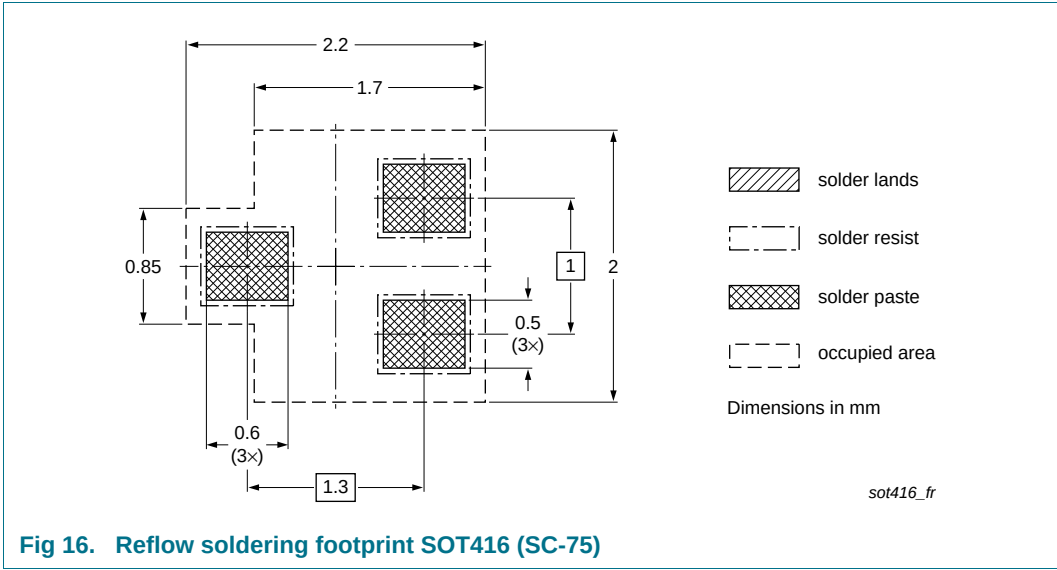


Fig 16. Reflow soldering footprint SOT416 (SC-75)

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846_SER v.9	20120925	Product data sheet	-	BC846_SER v.8
Modifications:	• Table 6 "Limiting values" : P_{tot} values corrected			
BC846_SER v.8	20120424	Product data sheet		BC846_BC546_SER v.7
BC846_BC546_SER v.7	20091117	Product data sheet	-	BC846_BC546_SER v.6
BC846_BC546_SER v.6	20060207	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	3
7	Characteristics	4
8	Package outline	7
9	Packing information	8
10	Soldering	9
11	Revision history	12
12	Legal information	13
12.1	Data sheet status	13
12.2	Definitions	13
12.3	Disclaimers	13
12.4	Trademarks	14
13	Contact information	14
14	Contents	15

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